Supporting Information:

Scalable and selective dispersion of semiconducting arcdischarged carbon nanotubes by dithiafulvalene/thiophene copolymers for thin film transistors

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Figure S1. AFM images of the morphology of (a) small-diameter (0.7nm~1.1nm) Hipco SWNTs and large-diameter(~1.4nm) Arc-discharge SWNTs.



Figure S2. Absorption spectrums of the SWNTs dispersed by pDTFF-mT on films after polymer burning process.



Figure S3. Transfer curve of a pDTFF-3T device (without SWNTs) in the saturation regime ($I_{SD} = -120V$).



Figure S4. AFM images of the device made from large-diameter SWNTs with a density of (a) ~15 SWNTs/ μ m² (b) ~50 SWNTs/ μ m² dispersed by pDTFF-3T in toluene.



Figure S5. AFM images of the device made from large-diameter SWNTs with a density of \sim 30 SWNTs/µm² dispersed by pDTFF-3T in chloroform.



Figure S6. Small angle X-ray scattering (SAXS) profiles of pDTFF-1T (red), pDTFF-2T (blue) and pDTFF-3T (green).



Figure S7. Starting structure of the MD simulation for (a) (11,8) m-SWNT and (b) (16,6) sc-SWNT.

	Mn (g/mol)	PDI
pDTFF-1T	3.2 x 10 ⁴	1.2
pDTFF-2T	8.4 x 10 ⁴	1.9
pDTFF-3T	5.0 x 10 ⁴	2.1

Table S1. Molecular weight and polydispersity of polymers measured by GelPermeation Chormatography (GPC).